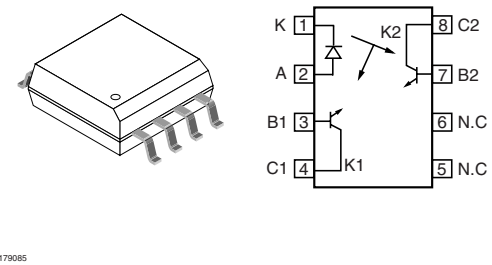
Linear Optocoupler, PCMCIA Package



i179085

FEATURES

- 2.3 mm high SMD package
- High sensitivity (K1) at low operating LED current
- Couples AC and DC signals
- Low input-output capacitance
- Isolation test voltage, 2130 V_{DC}
- Low distortion, below - 80 db
- 0.4 mm internal insulation thickness
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

RoHS COMPLIANT

APPLICATIONS

- Optical DAA for V.34 FAX/modem PCMCIA cards
- Digital telephone line isolation

DESCRIPTION

The IL388 family of linear optocoupler consist of an IRLED optically coupled to two photodiodes. The emitter is located such that both photodiodes receive approximately an equal amount of infrared light. The diodes produce a proportional amount of photocurrents. The ratio of the photocurrents stays constant with high accuracy when either the LED current changes or the ambient temperature changes. Thus one can control the output photodiode current.

The IL388 optocouplers can be used with the aid of operational amplifiers in closed loop conditions to achieve highly linearly and electrically AC and or DC signals amplifiers.

ORDER INFORMATION

PART	REMARKS
IL388	Couples AC and DC signals, SOP-8

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	≤ 3.0	V
Forward current		I_F	≤ 30	mA
Surge current pulse width < 10 µs		I_{PK}	≤ 150	mA
Power dissipation		P_{diss}	≤ 150	mW
Derate linearly from 25 °C			≤ 2.0	mW/°C
Junction temperature		T_j	≤ 100	°C
OUTPUT				
Reverse voltage		V_R	≤ 15	V
Power dissipation		P_{diss}	≤ 50	mW
Derate linearly from 25 °C			≤ 0.65	mW/°C
Junction temperature		T_j	≤ 100	°C

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	**TEST CONDITION**	**SYMBOL**	**VALUE**	**UNIT**
COUPLER				
Isolation test voltage		V_{ISO}	≤ 2130	V_{DC}
Total package power dissipation		P_{tot}	≤ 250	mW
Derate linearly from 25 °C			≤ 2.8	mW/°C
Storage temperature		T_{stg}	- 40 to + 150	°C
Operating temperature		T_{amb}	0 to + 75	°C
Lead soldering time at 260 °C			≤ 10	s
Isolation resistance	V_{IO} = 500 V, T_{amb} = 25 °C	R_{IO}	$\geq 10^{12}$	Ω
	V_{IO} = 500 V, T_{amb} = 100 °C	R_{IO}	$\leq 10^{11}$	Ω

Note

T_{amb} = 25 °C, unless otherwise specified.
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTCS							
PARAMETER	**TEST CONDITION**	**PART**	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
INPUT							
Forward voltage	I_F = 10 mA		V_F		1.8	2.1	V
Reverse current	V_R = 3.0 V		I_R		0.01	10	µA
V_F temperature coefficient			$\Delta V_F/\Delta$ °C		- 2.2		mW/°C
Junction capacitance	V_F = 0 V, f = 1.0 MHz		C_j		15		pF
Dynamic resistance	I_F = 10 mA		$\Delta V_F/\Delta I_F$		6.0		Ω
OUTPUT							
Junction capacitance	V_F = 0 V, f = 1.0 MHz		C_j		12		pF
AC Characteristics photovoltaic mode							
Frequency response	I_{P1} = 25 mA modulation current ΔI_{P1} = ± 6.0 µA		BW (- 3 db)		1.0	50	MHz
Phase response	I_{P1} = 25 mA modulation current ΔI_{P1} = ± 6.0 µA				45		°
Rise time	I_{P1} = 25 mA modulation current ΔI_{P1} = ± 6.0 µA		t_r		350		ns
COUPLER							
Capacitance (input to output)	V_F = 0 V, f = 1.0 MHz		C_{IO}		1.0		pF
Common mode capacitance	V_F = 0 V, f = 1.0 MHz		C_{CM}		0.5		pF
Coupled characteristics							
K_1	I_F = 2.0 mA, V_D = 0 V		K1	0.007			
THD	f_0 = 316, I_{PI} = 35 µA, V_D = 0 V			- 83			db
$K_3 = K_2/K_1$	I_F = 2.0 mA, V_D = 0 V			0.690		1.311	

Note

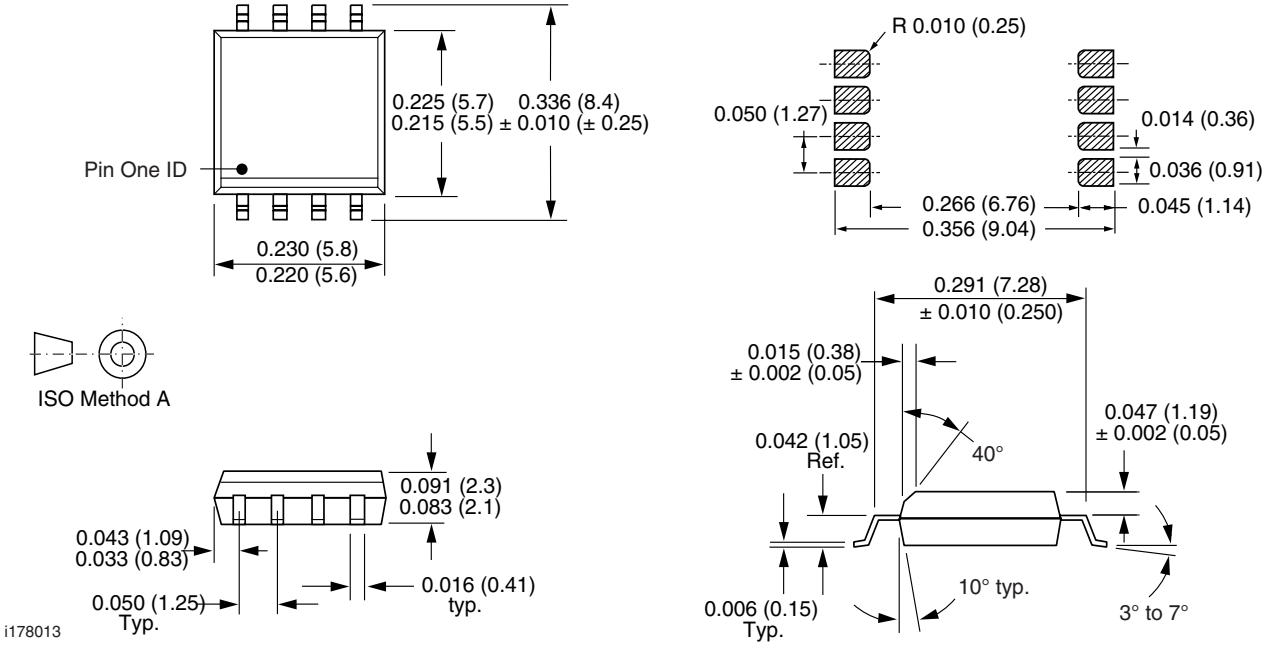
T_{amb} = 25 °C, unless otherwise specified.
Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

BIN TABLE FOR K_3		
BIN	**MIN.**	**MAX.**
C	0.690	0.773
D	0.765	0.859
E	0.851	0.955
F	0.945	1.061
G	1.051	1.181
H	1.169	1.311

Note

Binning categorization is for information only. Product cannot be ordered by this categorization.

PACKAGE DIMENSIONS in inches (millimeters)



OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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